

N-Channel Super Trench Power MOSFET

Description

The HMS35DN10DA uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(on)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

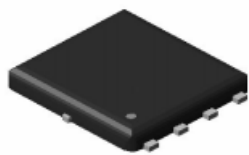
Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

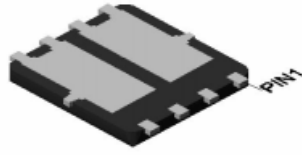
General Features

- $V_{DS} = 100V, I_D = 35A$
- $R_{DS(on)} = 18m\Omega$ (typical) @ $V_{GS} = 10V$
- $R_{DS(on)} = 22m\Omega$ (typical) @ $V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

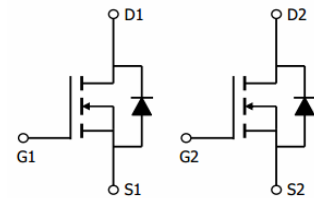
100% UIS TESTED!
100% ΔV_{ds} TESTED!



DFN 5X6



Top View



Schematic Diagram

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|-------------|----------------|-----------|------------|----------|
| HMS35DN10DA | HMS35DN10DA | DFN5X6-8L | | | |

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|--------------------|------------|---------------|
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 35 | A |
| Drain Current-Continuous($T_C = 100^\circ C$) | $I_D(100^\circ C)$ | 24.8 | A |
| Pulsed Drain Current | I_{DM} | 140 | A |
| Maximum Power Dissipation | P_D | 50 | W |
| Derating factor | | 0.4 | W/ $^\circ C$ |
| Single pulse avalanche energy ^(Note 5) | E_{AS} | 200 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | $^\circ C$ |

Thermal Characteristic

| | | | |
|--|-----------------|-----|--------------|
| Thermal Resistance, Junction-to-Case ^(Note 2) | $R_{\theta JC}$ | 2.5 | $^\circ C/W$ |
|--|-----------------|-----|--------------|

Electrical Characteristics (T_C=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---------------------|---|-----|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =250μA | 100 | | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =100V, V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 1.2 | 2.0 | 2.8 | V |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =10V, I _D =20A | - | 18 | 23 | mΩ |
| | | V _{GS} =4.5V, I _D =20A | - | 22 | 27 | mΩ |
| Forward Transconductance | g _{FS} | V _{DS} =5V, I _D =20A | - | 35 | - | S |
| Dynamic Characteristics (Note4) | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =50V, V _{GS} =0V, F=1.0MHz | - | 1600 | - | PF |
| Output Capacitance | C _{oss} | | - | 139 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | | - | 11 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | V _{DD} =50V, I _D =20A V _{GS} =10V, R _G =1.6Ω | - | 6 | - | nS |
| Turn-on Rise Time | t _r | | - | 2 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | | - | 18 | - | nS |
| Turn-Off Fall Time | t _f | | - | 2 | - | nS |
| Total Gate Charge | Q _g | V _{DS} =50V, I _D =20A, V _{GS} =10V | - | 26 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 7.4 | - | nC |
| Gate-Drain Charge | Q _{gd} | | - | 3.8 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V, I _S =35A | - | | 1.2 | V |
| Diode Forward Current (Note 2) | I _S | | - | - | 35 | A |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F = 20A di/dt = 500A/μs (Note3) | - | | 26 | nS |
| Reverse Recovery Charge | Q _{rr} | | - | | 98 | nC |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_J=25°C, V_{DD}=20V, V_G=10V, L=0.5mH, R_G=25Ω

Typical Electrical and Thermal Characteristics

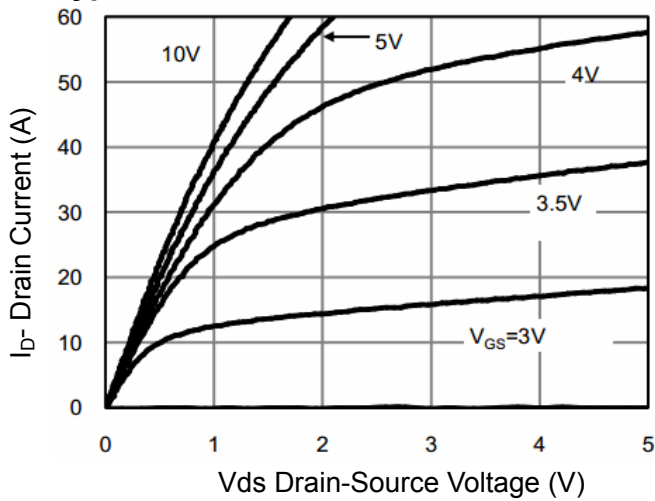


Figure 1 Output Characteristics

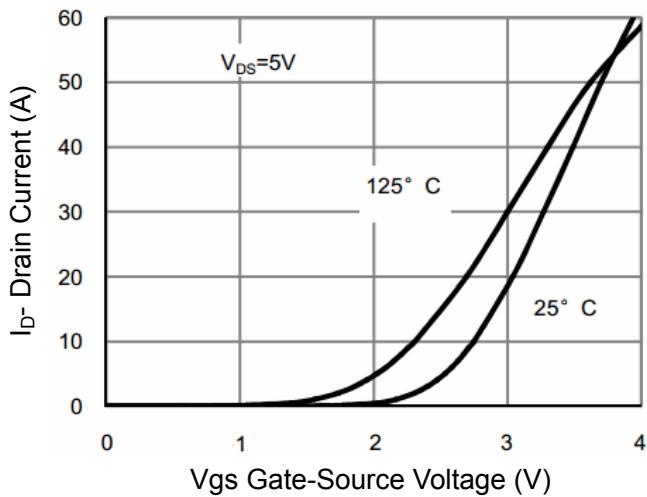


Figure 2 Transfer Characteristics

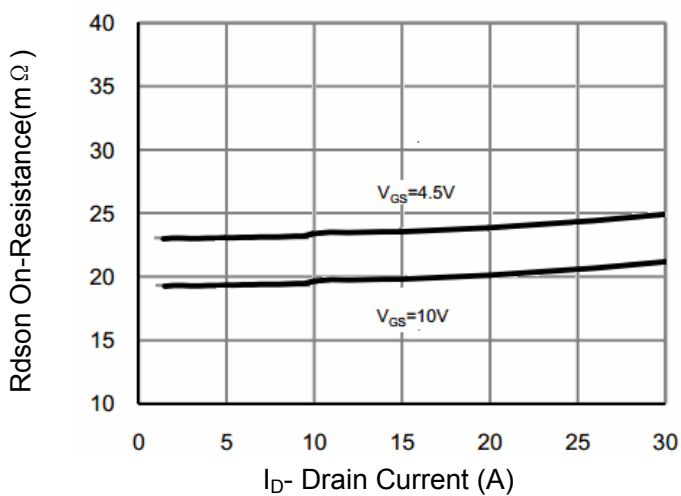


Figure 3 Rdson- Drain Current

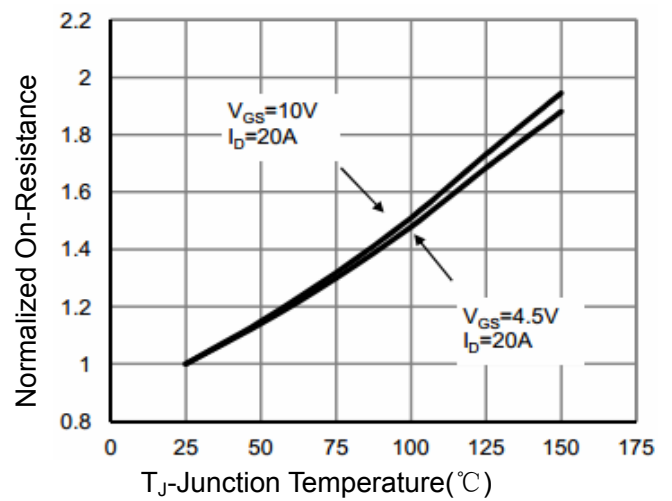


Figure 4 Rdson-Junction Temperature

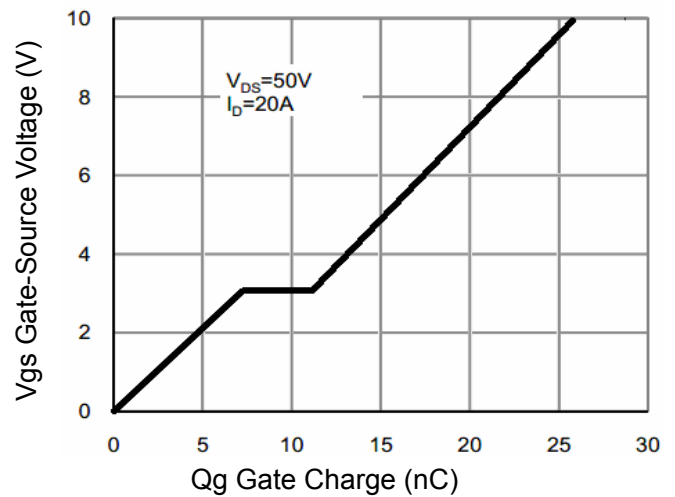


Figure 5 Gate Charge

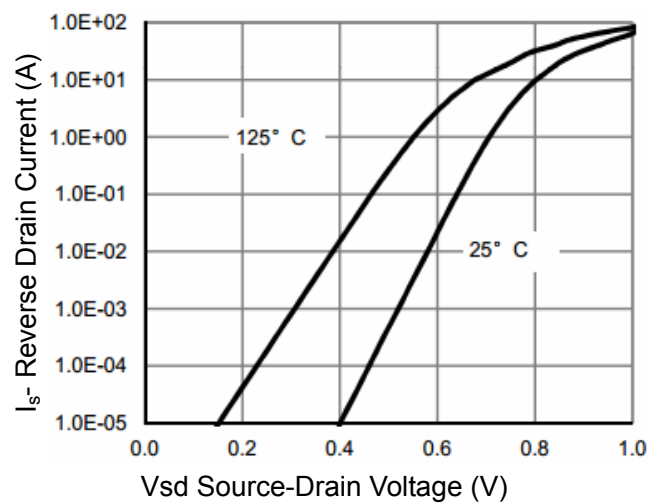


Figure 6 Source- Drain Diode Forward

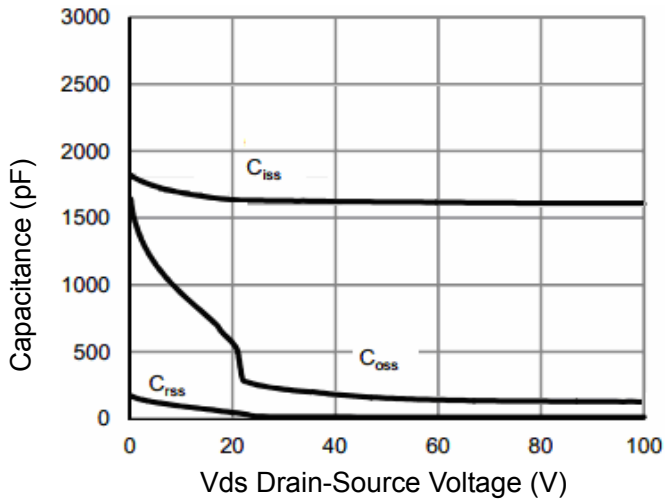


Figure 7 Capacitance vs Vds

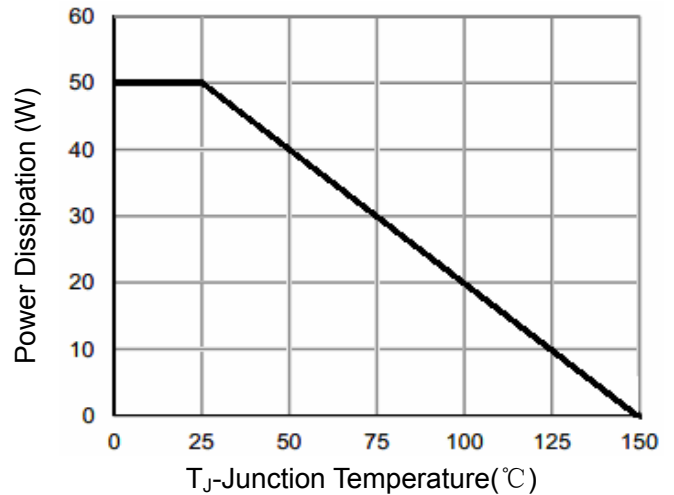


Figure 9 Power De-rating

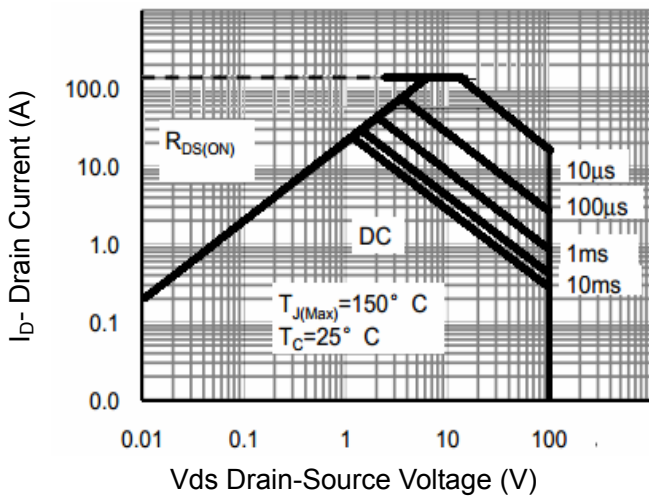


Figure 8 Safe Operation Area

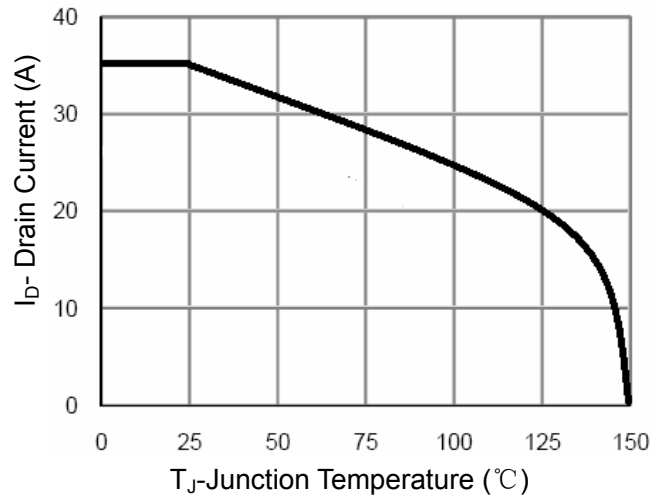


Figure 10 Current De-rating

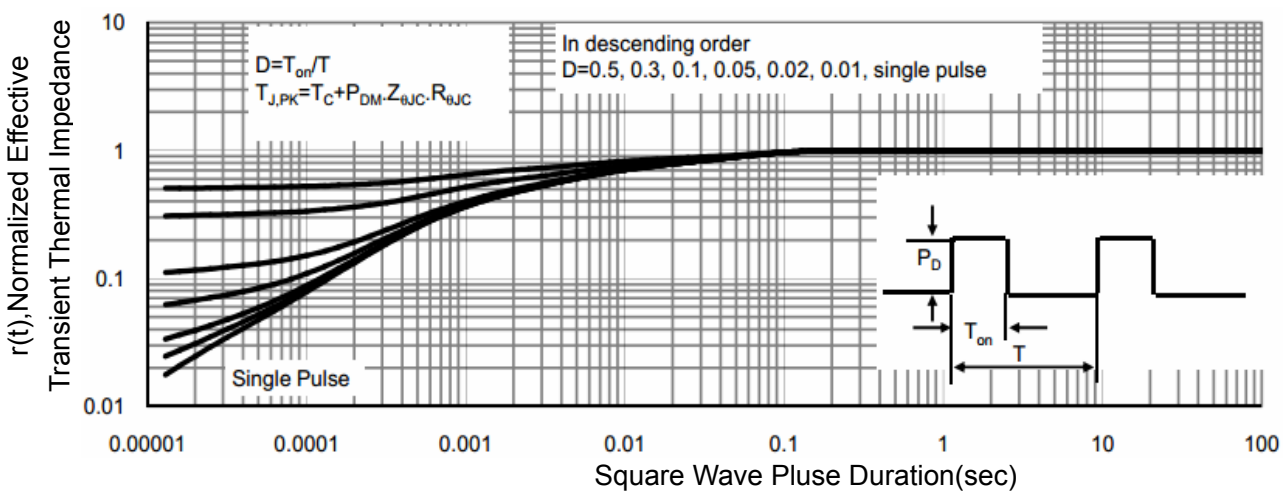
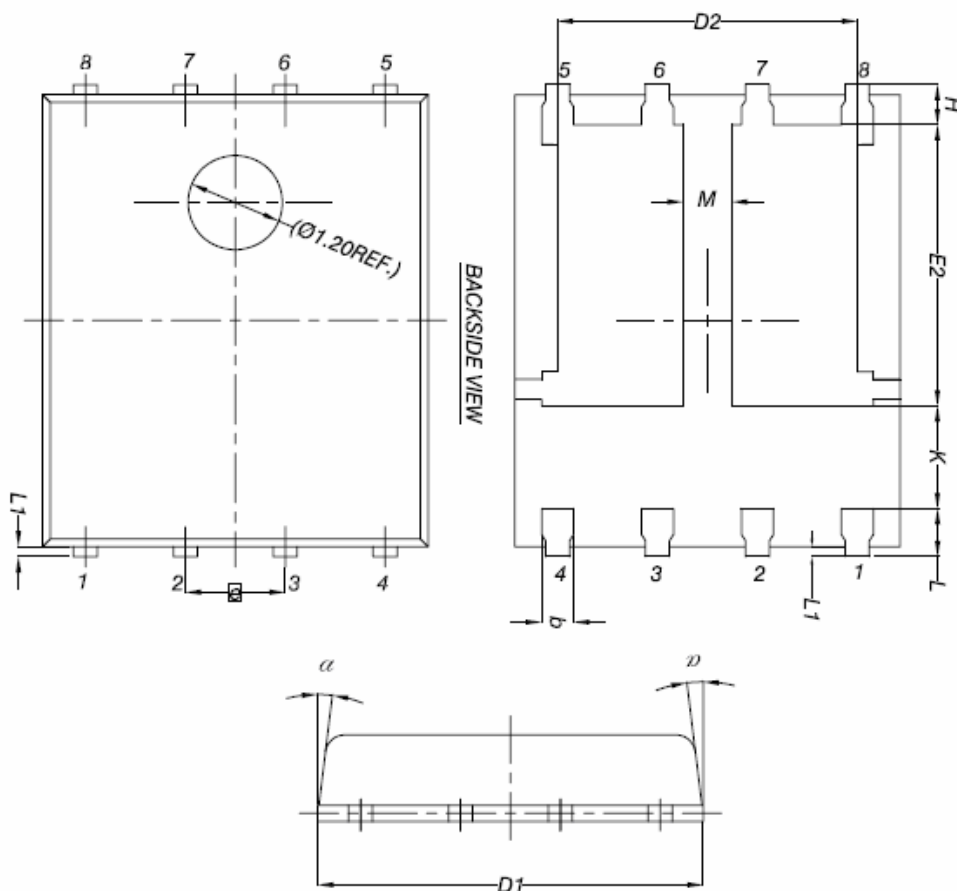


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



| DIM. | MILLIMETERS | | |
|----------|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.90 | 1.00 | 1.10 |
| b | 0.33 | 0.41 | 0.51 |
| C | 0.20 | 0.25 | 0.30 |
| D1 | 4.80 | 4.90 | 5.00 |
| D2 | 3.61 | 3.81 | 3.96 |
| E | 5.90 | 6.00 | 6.10 |
| E1 | 5.70 | 5.75 | 5.80 |
| E2 | 3.38 | 3.58 | 3.78 |
| e | 1.27 BSC | | |
| H | 0.41 | 0.51 | 0.61 |
| K | 1.10 | - | - |
| L | 0.51 | 0.61 | 0.71 |
| L1 | 0.06 | 0.13 | 0.20 |
| M | 0.50 | - | - |
| α | 0° | - | 12° |

